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## List of reference symbols

- 100 First experimentation arrangement
- 101 Platinum substrate
- 102 Silver sulfide tip
- 103 First voltage
- 104 Quantum point contact
- 110 Second experimentation arrangement
- 111 Second voltage
- 200 Graph
- 201 Abscissa
- 202 Ordinate
- 300 Layer sequence
- 301 Silicon substrate
- 302 Silicon oxide layer
- 303 Photoresist
- 304 Gold material
- 305 Trench
- 310 Layer sequence
- 311 Gold electrode
- 312 SAM layer
- 313 Chalcogenide electrode
- 320 Layer sequence
- 321 Cavity
- 330 Layer sequence
- 400 Memory cell arrangement
- 401 Gold bit lines
- 402 Chalcogenide word lines
- 500 Memory cell
- 501 First electrode
- 502 Second electrode
- 503 Cavity
- 504 First source/drain region
- 505 Second source/drain region
- 506 Surrounded gate region
- 600 Memory cell
- 601 First chalcogenide electrode
- 602 Second chalcogenide electrode

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603 Silver electrode

604 Bridging structure